



PATENT
0465-0636P

IN THE U.S. PATENT AND TRADEMARK OFFICE

Applicant: YANG, Hae C. Conf. No.: 1780
Appl. No.: 09/452,809 Group: 2814
Filed: December 2, 1999 Examiner: Dana Farahat
For: ESD PROTECTION CIRCUIT AND METHOD FOR
FABRICATING THE SAME

#7/B
5/2/02
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AMENDMENT

Honorable Commissioner of Patents
Washington, D.C. 20231

May 10, 2002

Sir:

In response to the Examiner's Office Action dated February 11, 2002, the following amendments and remarks are respectfully submitted in connection with the above-identified application.

In the Specification:

Please replace the paragraph beginning on page ²1, line 7, with the following rewritten paragraph:

+Fig. 1 illustrates a system of a related art ESD protection circuit. In general, a maximum field strength against which an oxide film in an MOS transistor can endure is 6MV/cm, which corresponds to 30V if the oxide film is scaled up to a thickness of 50nm. A voltage of this magnitude can be easily